

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D T _C = +25°C
60V	40mΩ @ V _{GS} = 10V	20A
	58mΩ @ V _{GS} = 4.5V	16A

Features

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

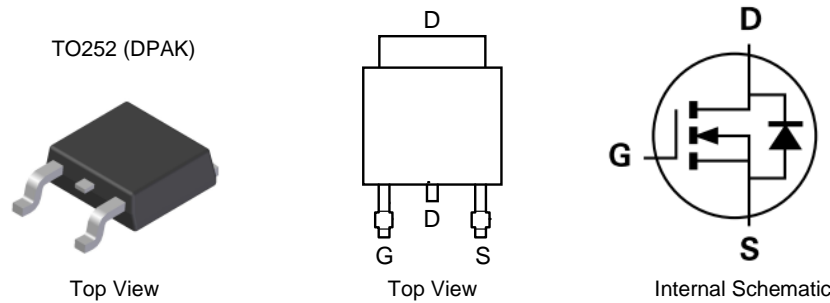
Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Backlighting

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)

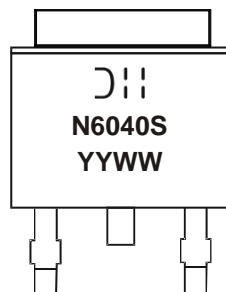


Ordering Information (Note 5)

Part Number	Case	Packaging
DMN6040SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
 5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- DII = Manufacturer's Marking
- N6040S = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Last Two Digits of Year (ex: 18 = 2018)
- WW = Week Code (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_C = +25^\circ\text{C}$	I_D	20	A
		$T_C = +100^\circ\text{C}$		13	
Maximum Body Diode Forward Current (Note 6)			I_S	4	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	30	A
Avalanche Current (Note 7)			I_{AS}	14.2	A
Avalanche Energy (Note 7)			E_{AS}	10	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_C = +25^\circ\text{C}$	P_D	42	W
	$T_C = +100^\circ\text{C}$		17	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	44	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	30	40	m Ω	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	35	58		$V_{GS} = 4.5\text{V}, I_D = 12\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1,287	—	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	57	—		
Reverse Transfer Capacitance	C_{rss}	—	44	—		
Gate Resistance	R_G	—	1.2	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	22.4	—	nC	$V_{DS} = 30\text{V}, I_D = 4.3\text{A}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	10.4	—		
Gate-Source Charge	Q_{gs}	—	4.9	—		
Gate-Drain Charge	Q_{gd}	—	3.0	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.6	—	ns	$V_{GS} = 10\text{V}, V_{DD} = 30\text{V}, R_G = 6\Omega,$ $I_D = 4.3\text{A}$
Turn-On Rise Time	t_R	—	8.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	20.1	—		
Turn-Off Fall Time	t_F	—	4.0	—		
Body Diode Reverse Recovery Time	t_{RR}	—	18	—	ns	$I_S = 4.3\text{A}, dI/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	11.9	—	nC	$I_S = 4.3\text{A}, dI/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 - UIS in production with $L = 0.1\text{mH}$, $T_J = +25^\circ\text{C}$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

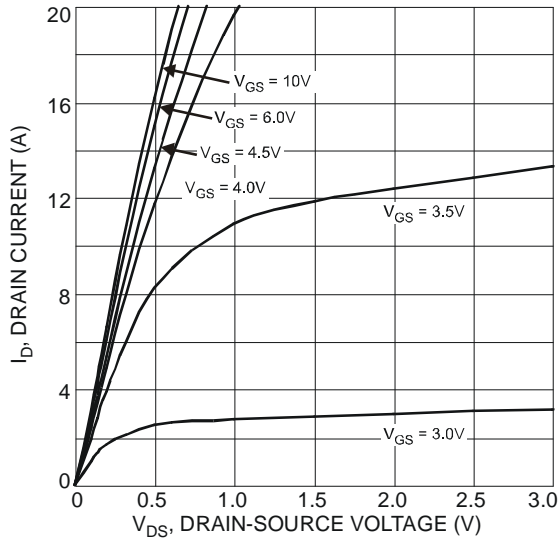


Fig. 1 Typical Output Characteristic

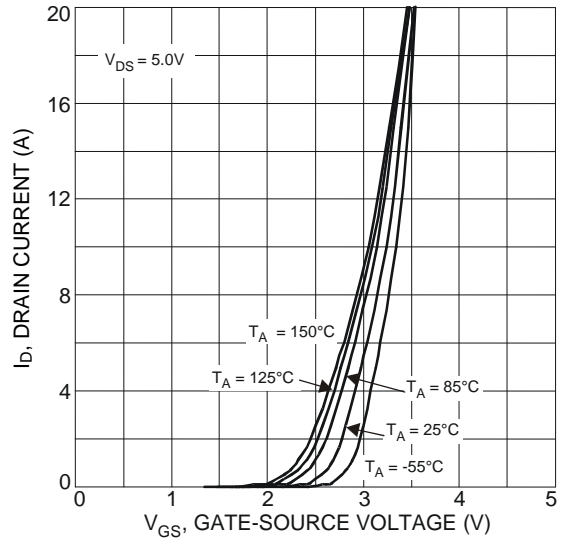


Fig. 2 Typical Transfer Characteristics

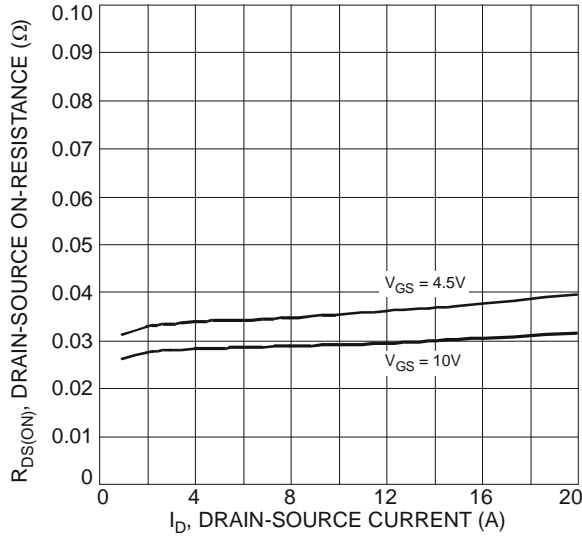


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

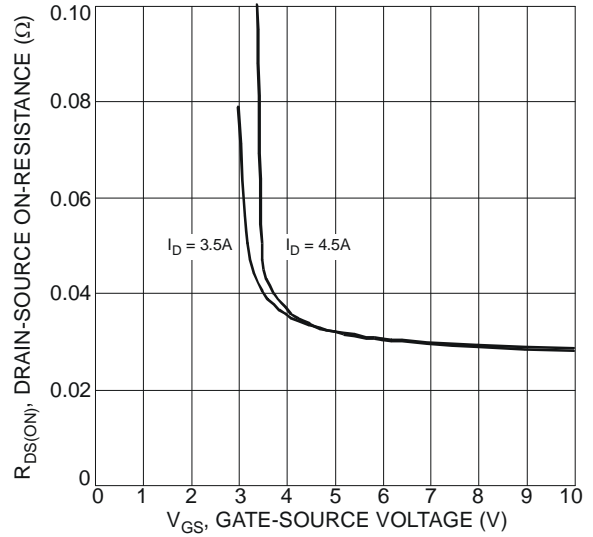


Fig. 4 Typical On-Resistance vs. Drain Current and Gate Voltage

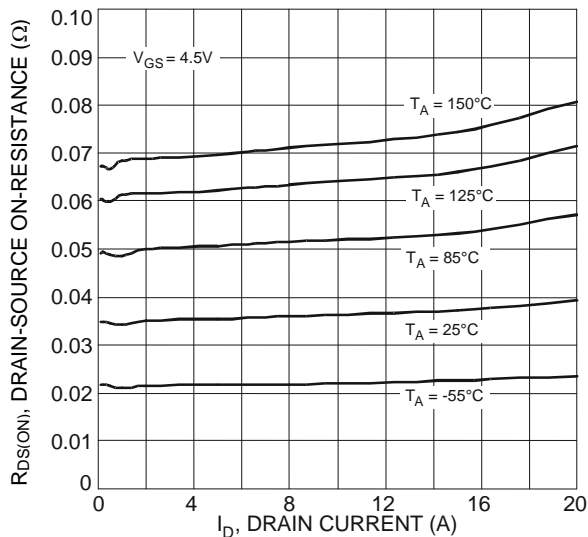


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

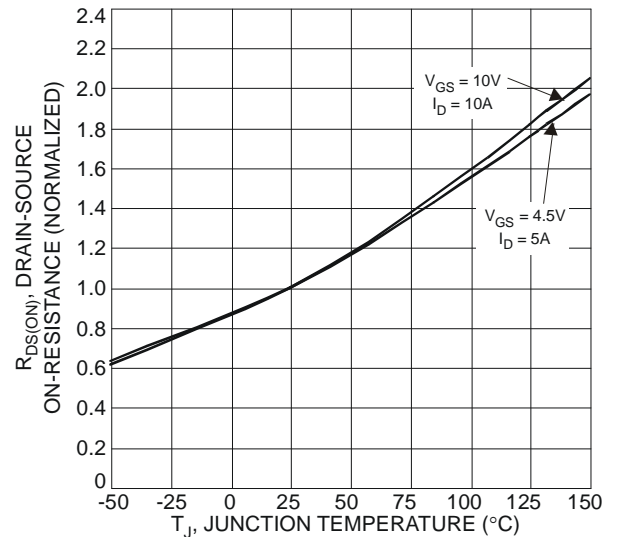


Fig. 6 On-Resistance Variation with Temperature

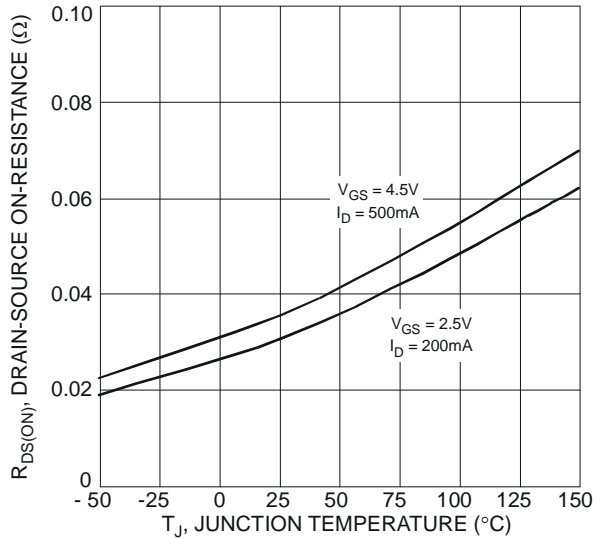


Fig. 7 On-Resistance Variation with Temperature

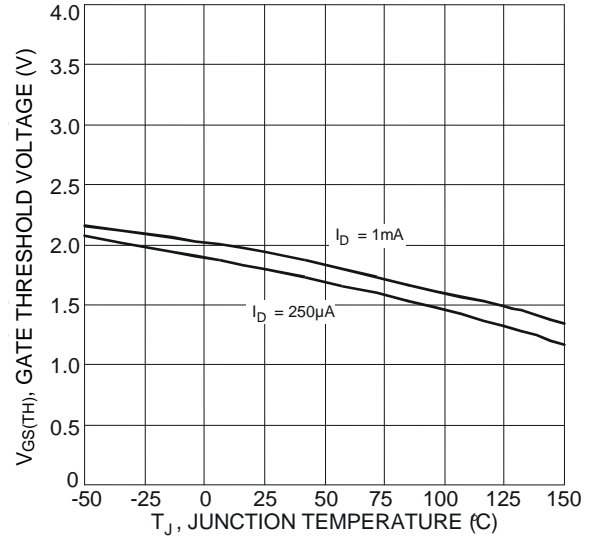


Fig. 8 Gate Threshold Variation vs. Junction Temperature

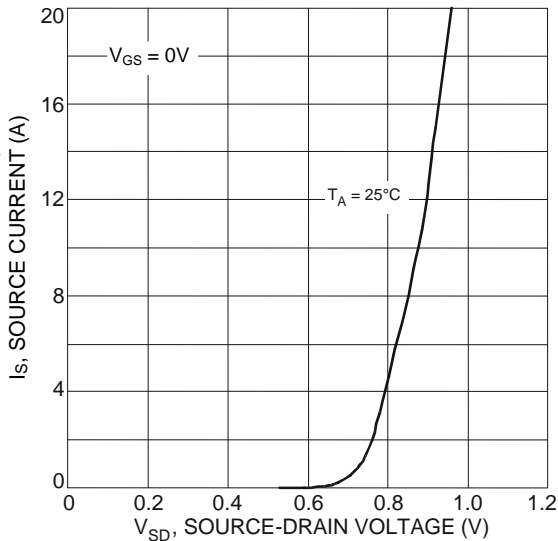


Fig. 9 Diode Forward Voltage vs. Current

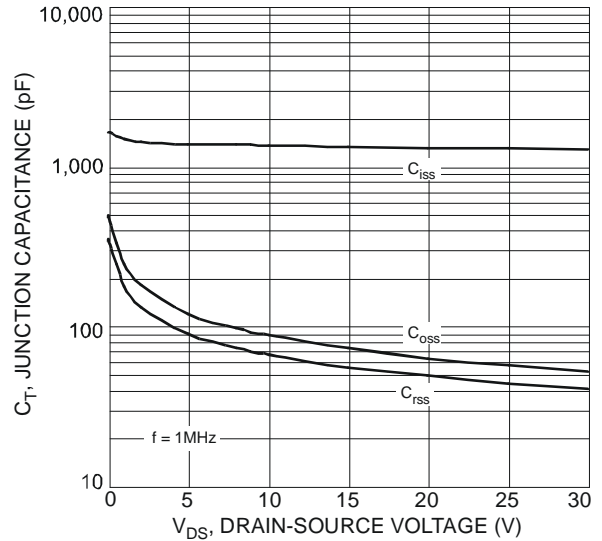


Fig. 10 Typical Junction Capacitance

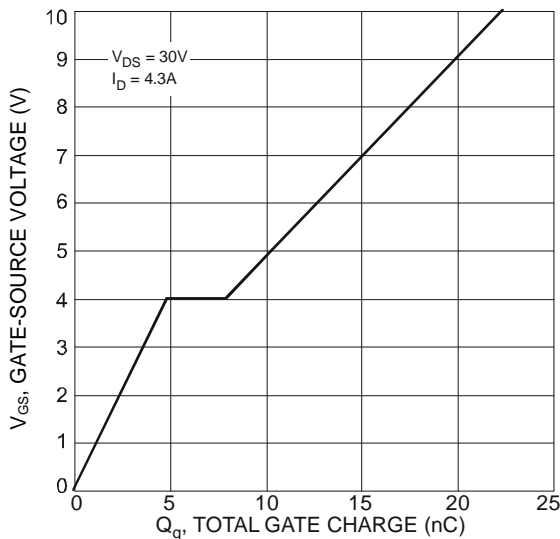


Fig. 11 Gate Charge

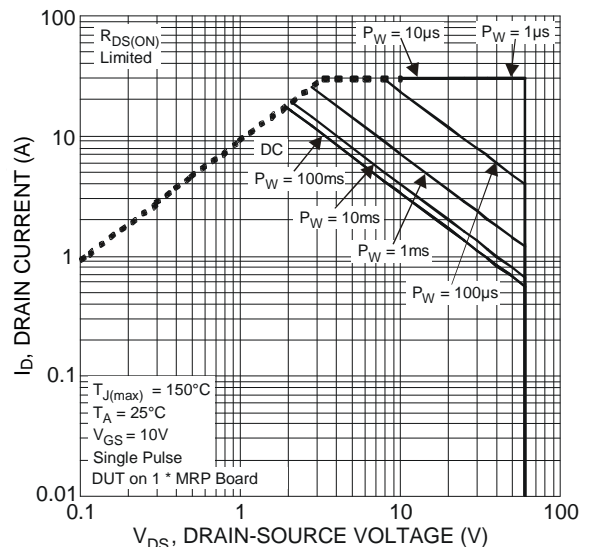
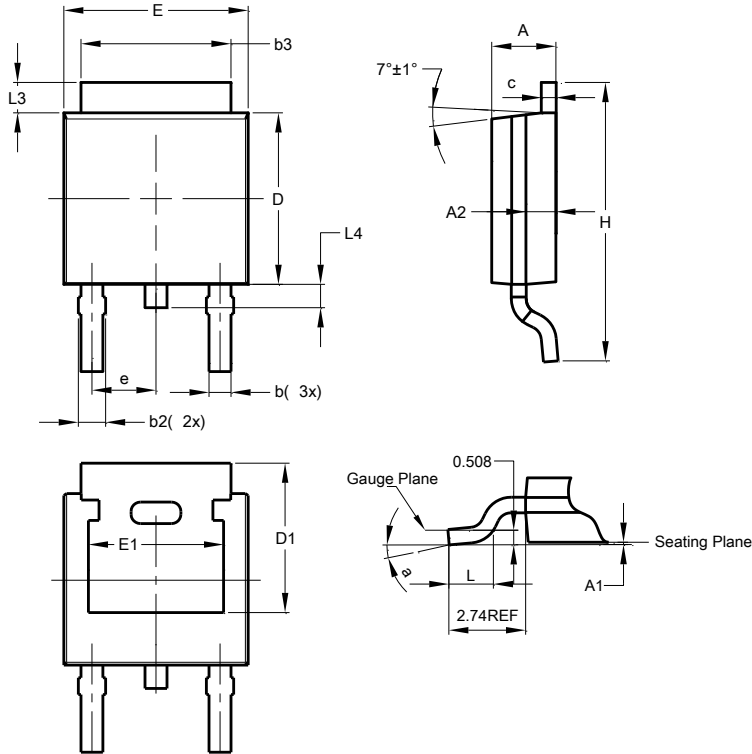


Fig. 12 SOA, Safe Operation Area

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

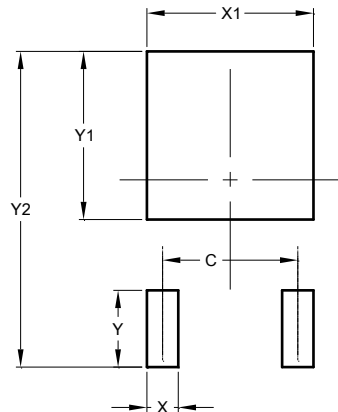


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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